L Number	Hits	Search Text	DB	Time stamp
6	980	(plasma near etch$3) and (copper near plat$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 15:09
7	699	(plasma near etch$3) and (copper near plat$3)	USPAT	2004/09/06 15:09
-	2	("20040063263").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 11:15
-	1746	438/197	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 10:46
-	45	438/197 and (backside or (back near side))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 11:23
-	17120	(cleaning same wafer) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 11:23
-	2345	((cleaning same wafer) and semiconductor) and (plasma near etch$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 11:37
-	129	Toledo.xa.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 11:40
-	259	(wafer near clean$3) and semiconductor and (protective near (flim or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 15:27
-	68476	Nakajima.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 15:29
-	206	Nakajima.in. and (protective and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 15:30
-	51	(Nakajima.in. and (protective and semiconductor)) and CVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:46
-	0	"300.mm." and wafer and (clean$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:47
-	0	"300.mm." near wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:47

-	0	"300.mm."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:47
-	16321	"300" same wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:52
-	6545	("300" same wafer) and clean$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:52
-	1494	(("300" same wafer) and clean$3) and (plasma near etch$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:53
-	5834	(("300" same wafer) and clean$3) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:48
-	1390	((("300" same wafer) and clean$3) and (plasma near etch$3)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:53
-	645	(((("300" same wafer) and clean$3) and (plasma near etch$3)) and semiconductor) and (copper or Cu)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:53
-	39	((((("300" same wafer) and clean$3) and (plasma near etch$3)) and semiconductor) and (copper or Cu)) and STI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 17:10
-	2722	"300 mm" same wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:52
-	1456	("300 mm" same wafer) and clean$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:52
-	335	(("300 mm" same wafer) and clean$3) and (plasma near etch$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:53
-	330	((("300 mm" same wafer) and clean$3) and (plasma near etch$3)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:53
-	132	(((("300 mm" same wafer) and clean$3) and (plasma near etch$3)) and semiconductor) and (copper or Cu)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 16:53
-	10	((((("300 mm" same wafer) and clean$3) and (plasma near etch$3)) and semiconductor) and (copper or Cu)) and STI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 15:08

-	13	(backside near polish$3) same (mirror) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 17:15
-	235	Maydan.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 17:15
-	333	Denning.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 11:34
-	163	Denning.in.	USPAT	2004/09/06 11:37
-	22	Kraft.in. and nitride	USPAT	2004/09/06 11:39
-	6688	copper near plating	USPAT	2004/09/06 11:40
-	10	(copper near plating) and STI	USPAT	2004/09/06 11:40